

**Inchange Semiconductor**

**Product Specification**

**Silicon NPN Power Transistors**

**2SC1469**

**DESCRIPTION**

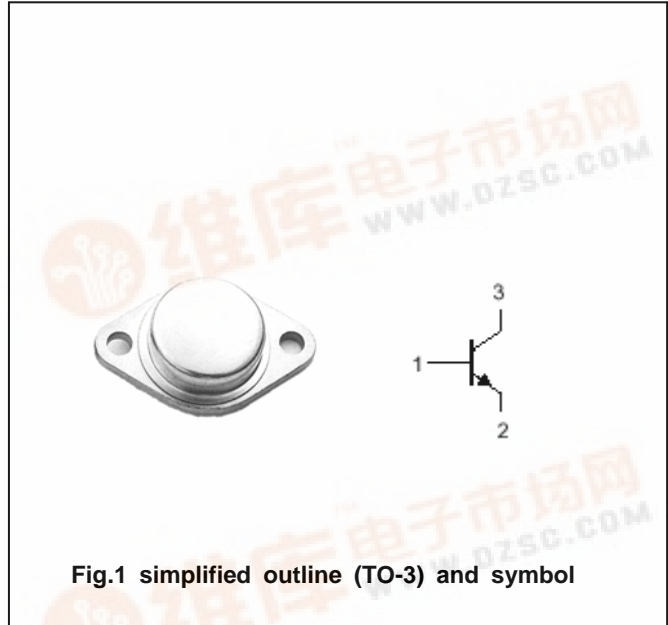
- With TO-3 package
- High breakdown voltage

**APPLICATIONS**

- For high voltage ,fast switching applications

**PINNING (See Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	500	V
$V_{CEO}$	Collector-emitter voltage	Open base	400	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		10	A
$I_B$	Base current		4	A
$P_T$	Total power dissipation	$T_C \leq 25^\circ C$	100	W
$T_j$	Junction temperature		200	$^\circ C$
$T_{stg}$	Storage temperature		-65~200	$^\circ C$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.25	$^\circ C/W$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	400			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A ; I <sub>B</sub> =1A			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =500V ; I <sub>E</sub> =0			0.1	mA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =400V ; I <sub>B</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V ; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	15		50	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =5V	8			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V		10		MHz

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PACKAGE OUTLINE

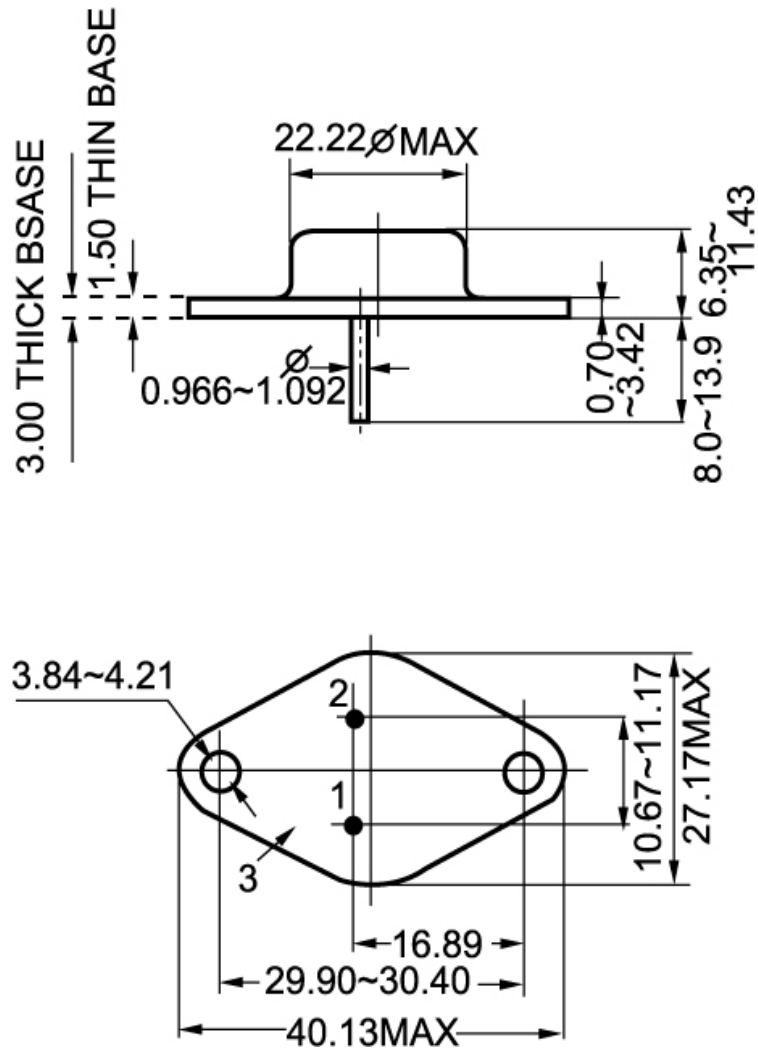


Fig.2 Outline dimensions